Contents lists available at ScienceDirect

Electrochemistry Communications

journal homepage: www.elsevier.com/locate/elecom

Short communication

Thiol anchoring and catalysis of gold nanoparticles at the liquid interface of thin-organic film-modified electrodes



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ARTICLE INFO

Article history: Received 29 October 2013 Received in revised form 19 November 2013 Accepted 21 November 2013 Available online 28 November 2013

Keywords: Thin-organic-film electrodes Liquid/liquid interface Gold nanoparticles

ABSTRACT

The deposition of in-situ formed gold nanoparticles at the liquid/liquid (L/L) interface is studied by means of thin-organic-film-modified electrodes (TFE). The degree of ordering and aggregation of gold nanoparticles can be tuned by adding a lipophilic and hydrophilic thiol in the organic and aqueous phase, respectively. The ordered thiol-anchored gold nanoparticles exhibit pronounced catalytic effect toward electron-transfer reactions across the L/L interface.

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1. Introduction

Thin-organic-film-modified electrodes (TFE) [1], together with the droplet-electrodes (i.e. the three-phase electrodes) [2], are a useful tool for studying complex electrochemical processes where the electrode reaction is coupled with an ion-transfer across a L/L interface. Their application ranges from determination of thermodynamic [2,3] and kinetic parameters of ion [4,5] and/or electron transfers [1,6], mechanistic [7] and biomimetic studies of membrane processes [8], to bioelectroanalysis [9,10]. Besides, it has been demonstrated that TFE are an excellent scaffold for studying metal nanoparticle deposition at the L/L interfaces [11], which is a unique environment due to its molecular smoothness [12]. Owing to the pronounced sensitivity of the voltammetric response of TFE to the properties of the liquid interfacial region, the aggregation of nanoparticles can be effectively examined by means of voltammetric techniques [11]. The study of metal particles synthesis and deposition at the L/L interface of TFE is justified for several reasons; e.g., it is a root for additional surface modification for advanced analytical applications [13,14], or it is a valuable approach for studying the catalytic properties of metal nanoparticles at the L/L interface [15-18].

In the present communication we demonstrate that gold nanoparticles can be effectively anchored at the nitrobenzene/water (NB/W) interface by means of a hydrophobic and hydrophilic thiols added to the organic and aqueous phase, respectively. Thiol-anchored gold nanoparticles effectively block the ion transfers, while significantly accelerate the heterogeneous electron transfers across the NB/W interface.

2. Experimental

All chemicals were of analytical grade purity. Decamethylferrocene (DMFC) was purchased from Fluka. Other chemicals (cysteine, tetrabutylammonium perchlorate (Bu₄NClO₄), LiClO₄, thiophenol (PhSH), 1,1',4',1''-terphenyl-4-thiol (Ph₃SH), K[AuCl₄], K₂[PdCl₄], Hg(NO₃)₂, CuSO₄, ZnSO₄, K₃[Fe(CN)₆], and H₂O₂) were Merck products. Nitrobenzene solution contained 50 mmol/L DMFC and 0.1 mol/L (Bu₄NClO₄) as an organic electrolyte. For thiol experiments, PhSH or Ph₃SH was added to NB at 0.1 mmol/L, if not otherwise stated. A graphite rod (black graphite), GrafTech, UCAR SNC, La Lechere France (0.113 cm diameter) was a working electrode. After cleaning of the electrode surface ca. 0.3 µL NB-solution was imposed, a thin film forming by spontaneous spreading of the solution. 0.1 mol/L LiClO₄ served as an aqueous electrolyte solution.

An Ag/AgCl (3 mol/L KCl) was a reference, while Pt wire served as an auxiliary electrode. Cyclic voltammetry (CV) has been conducted at µAUTOLAB III potentiostat/Galvanostat (Eco-Chemie, Netherlands).

Atomic forced microscopy (AFM) measurements were carried out using a scanning probe microscope, model SPM-9600 by Shimadzu. Imaging was performed in tapping mode and height, amplitude as well as phase images were recorded. Au deposits, prepared onto squared glass substrates (7 mm \times 7 mm), were placed on a sample holder (15 nm diameter) and measured in 3 μ m, 2 μ m and 1 μ m scale with a scan rate of 1 Hz and resolution of 256 lines per scan direction.



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^{1388-2481/\$ -} see front matter © 2013 Elsevier B.V. All rights reserved. http://dx.doi.org/10.1016/j.elecom.2013.11.020

The measurements were done using silicon cantilever with the following characteristics: frequency of 320 kHz and force constant of 42 N/m. A lot of different points on the sample surface were explored. The recorded images were just flattened and no additional processing was performed.

Raman spectra were recorded on a MicroRaman 300 (Horiba Jobin-Yvon), employing a green Nd–Yag 532 nm laser line and a longdistance \times 50 lens (Olympus) objective. The maximum unfiltered power on the sample was 1.08 mW. The integration time was 60 s, for the Raman shift from 100 cm⁻¹ to 4000 cm⁻¹. A diffraction grid with 1800 grooves/mm was used.

3. Results and discussion

The metal deposition at the L/L interface of TFE is a consequence of the spontaneous electron-transfer reaction between DMFC embedded in the organic phase and the corresponding metal ions in the aqueous phase, coupled with a corresponding ion transfer to maintain the charge neutrality of the two liquid phases (reaction (1)), as originally demonstrated by Cheng and Schiffrin [19]. The heterogeneous redox reaction (1) and the metal deposit are mainly localized at the L/L interface affecting strongly its properties.

$$n\text{DMFC}(\text{NB}) + \text{M}^{n+}(\text{W}) + n\text{ClO}_4^{-}(\text{W}) = \text{M}(\text{s}) + n\text{DMFC}^{+}(\text{NB}) + n\text{ClO}_4^{-}(\text{NB})$$
(1)

Commonly, in the absence of redox active species in the aqueous phase, the voltammetric response of TFE is owing to a complex electron-ion coupled electrochemical process (reaction (2)), where the electrode reaction of DMFC is coupled with a virtually simultaneous ion transfer across the NB/W interface [2,4,5].

$$DMFC(NB) + ClO_4^{-}(W) = DMFC^{+}(NB) + ClO_4^{-}(NB) + e^{-}$$
(2)

Moreover, for DMFC/ClO₄⁻ system, the kinetics of the overall electron-ion transfer reaction (2) is controlled by the rate of ClO₄⁻ transfer [4,5]. For these reasons, the voltammetric response of TFE is particularly sensitive to all phenomena affecting the properties of the L/L interface. In the presence of another redox species in the aqueous phase, the overall electrochemical reaction could additionally involve a heterogeneous electron-exchange reaction across the L/L interface [1,6].

In the course of the repetitive potential cycling the metal deposition is manifested as a decreasing of the voltammetric response (inset of Fig. 1A), as a consequence of the blocking of the L/L interface and hindering the ion transfer. The role of the standard potential difference between the two redox reactants, as a main driving force of the reaction (1), was examined by testing a series of metal cations, such as Au³⁺, Hg²⁺, Pd²⁺, Cu²⁺, and Zn²⁺. For all ions with $E_{M^{n+}/M}^{\varnothing}>E_{DMFC^+/DMFC}^{\oslash}$ (Au³⁺, Hg²⁺, Pd²⁺, Cu²⁺,) the decreasing of the response was observed (data not shown), implying an effective metal deposition. Only in the case of Zn²⁺ the voltammetric response was fully stable, implying no metal deposition as $E_{M^{n+}/M}^{\oslash} < E_{DMFC^+/DMFC}^{\oslash}$. As previously shown [12–14], the rate of the metal deposition and

As previously shown [12–14], the rate of the metal deposition and the morphology of the deposit depend on various factors, the most important being the reactant concentration ratio and the potential difference at the NB/W interface controlled by the partition of common ClO₄⁻ ions. For gold deposition, the morphology and ordering of the particles can be controlled by a thiol anchoring from both sides of the L/L interface. Fig. 1A summarizes the results collected in the absence (curve 1) and the presence of thiols (curves 2 and 3) deliberately added in the organic phase. The figure represents the current decrease (ΔI_p) as a function of the potential cycle serial number, i.e., $\Delta I_p = I_{p,a(n)} - I_{p,a(1)}$, where $I_{p,a(n)}$ and $I_{p,a(1)}$ are the anodic peak currents of the *n*-th and the first cyclic voltammogram. Hence, the peak current decreases in proportion to the progressive interface



Fig. 1. (A) The decreasing of the anodic peak current $(\Delta I_{a,p})$ as a function of the serial number of potential cycles recorded in the absence of thiol (1) and in the presence of 0.1 mmol/L PhSH (2) and Ph₃SH (3) in the organic phase. The aqueous phase contained 1 mmol/L K[AuCl₄] and 0.1 mol/L LiClO₄, while the organic phase contained 50 mmol/L DMFC and 0.1 mol/L Bu₄ClO₄. The inset shows repetitive cyclic voltammograms recorded in the absence of thiol (1) and in the presence of thiol (1) and in the presence of thiol (1) and in the presence of thiol. (B) AFM images of the gold deposit obtained in the absence of thiol (1) and in the presence of 1 mmol/L Ph₃SH in the organic phase (2). The gold deposition was ex-situ conducted by joining an aqueous and organic droplet of 0.5 µL volume on a glass plate and AFM images and Raman spectra have been taken after complete evaporation of the solvents. (C) Raman spectra of: (a) neat Ph₃SH (b) bare Au deposit, (c) glass on which the samples are deposited, (d) Au modified with Ph₃SH and (e) Au modified with Ph₃SH and cysteine.

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